

PMDPB30XN 20 V, dual N-channel Trench MOSFET

Product data sheet

Product profile 1.

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a small and leadless ultra thin DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Small brushless DC motor drive
- Power management in battery-driven portables
- Hard disc and computing power management

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	5.3	Α
Static characteristics (per transistor)							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$		-	32	40	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	6 5 4	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	7 8	(」☆本本☆↓)
4	S2	source TR2		
5	G2	gate TR2	1 2 3	G1 S1 S2 G2
6	D1	drain TR1	Transparent top view DFN2020-6 (SOT1118)	017aaa254
7	D1	drain TR1	51112020 3 (0011110)	
8	D2	drain TR2		

Ordering information

Table 3. **Ordering information**

Type number	Package				
	Name	Description	Version		
PMDPB30XN	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118		

Marking 4.

Marking codes Table 4.

Type number	Marking code
PMDPB30XN	1V

Limiting values 5.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V_{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	5.3	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	4	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	2.6	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	12	Α
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Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			[1]	-	1170	mW
		T _{sp} = 25 °C		-	8330	mW
Source-drai	n diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	1.2	Α
Per device			'		'	-
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

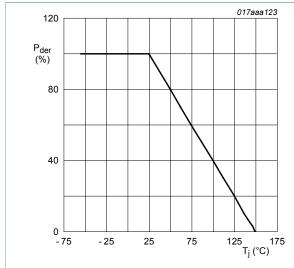


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

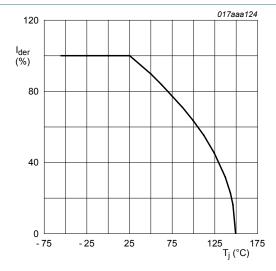
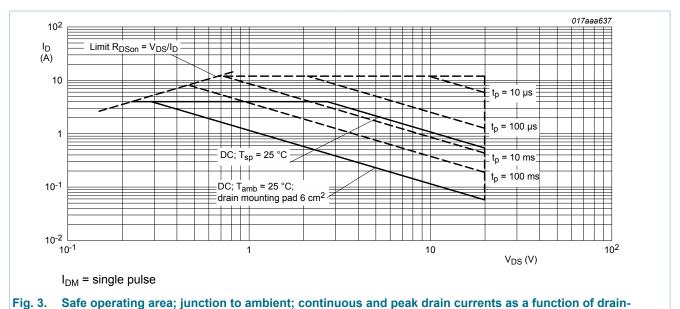


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Table 0. The	illiai Cilai acteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance	in free air	[1]	-	223	256	K/W
	1		[2]	-	93	107	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	55	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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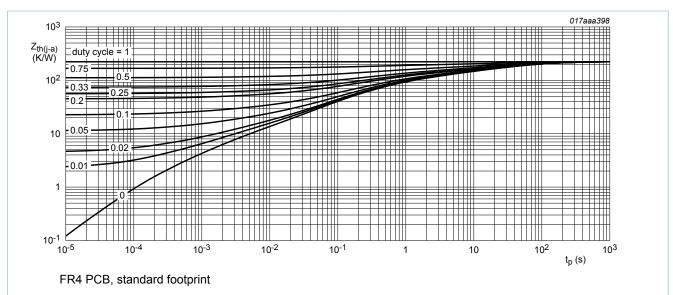


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

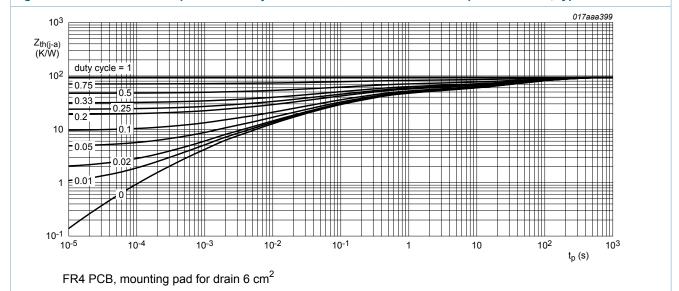


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics (per transistor)							
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		20	-	-	V
V_{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		0.4	0.65	0.9	V
I _{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	-	1	μA
		V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C		-	-	11	μA
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Unit
) nA
) nA
mΩ
mΩ
mΩ
mΩ
S
7 nC
nC
nC
pF
pF
pF
ns
ns
ns
ns
V
2

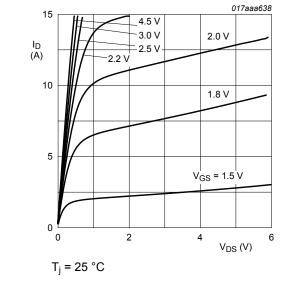


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

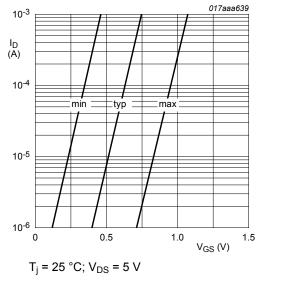


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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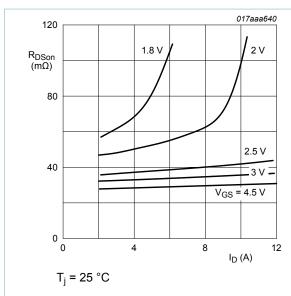


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

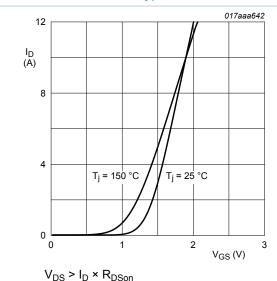


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

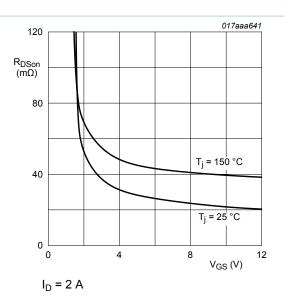


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

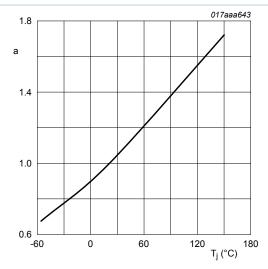


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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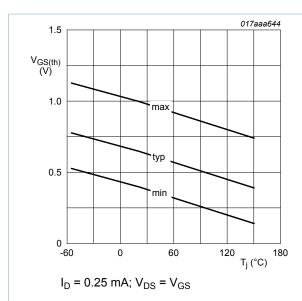


Fig. 12. Gate-source threshold voltage as a function of junction temperature

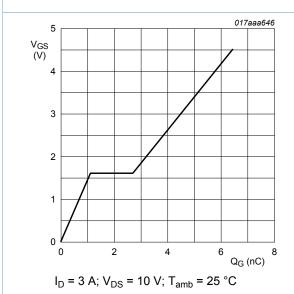


Fig. 14. Gate-source voltage as a function of gate charge; typical values

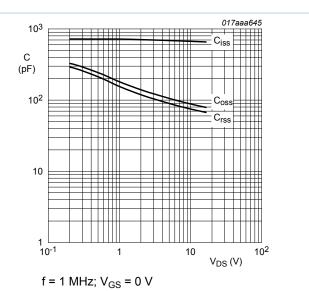


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

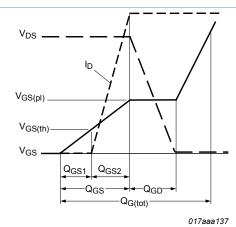
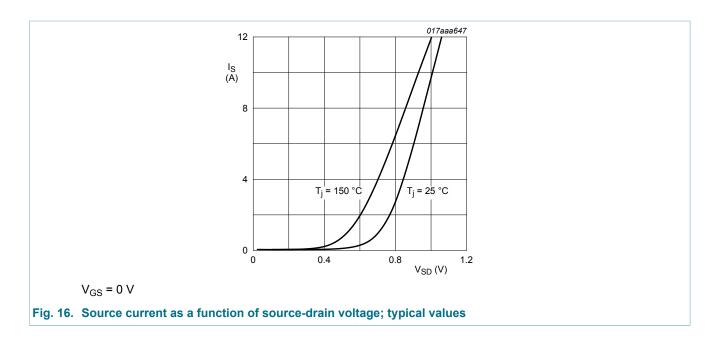
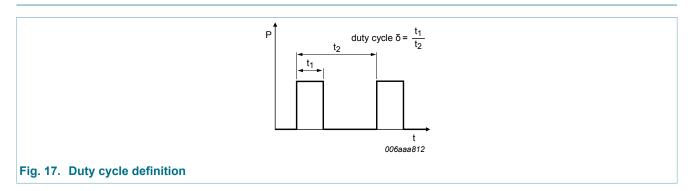


Fig. 15. Gate charge waveform definitions

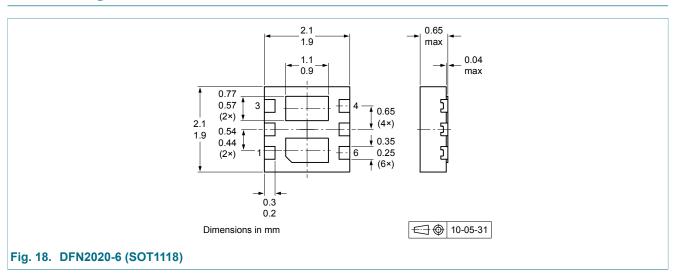
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8. Test information



9. Package outline



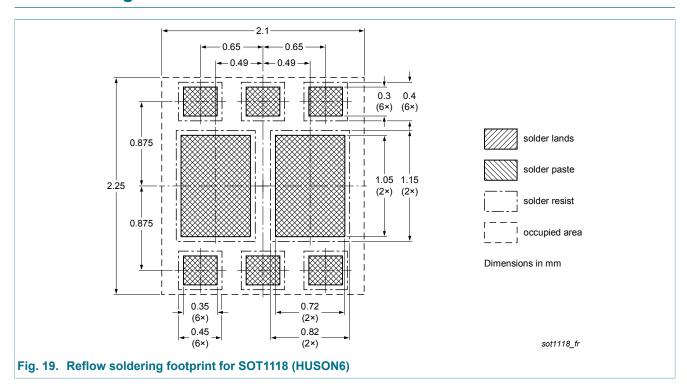
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10. Soldering



11. Revision history

Table 8. Revision history

Document ID	Release date	Document status	Change notice	Supersedes
PMDPB30XN v.1	20120706	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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